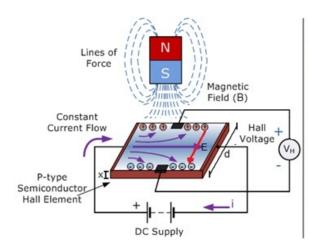
Hall Effect



- d width of semiconductor
- x thickness of semiconductor
- B external magnetic field
- V_H Hall Voltage
- I Current flowing in circuit
- E Electric field produced = VH/d
- A cross section area = d.x
- vd drift velocity

When a current carrying conductor semiconductor is kept in transverse magnetic field, the charge carriers of conductors or semiconductors experience a force perpendicular to both magnetic field and current, known as Hall Effect. In Semiconductors, at equilibrium, voltage appears at semiconductor edges called Hall Voltage.

Force due to Electric Field = qEForce due to Magnetic Field = qv_dB

Total Force
$$F = QE + QVaB$$

At Equilibrium $F = 0 \Rightarrow QE = -QVaB$
 $\Rightarrow Va = -\frac{E}{B} = -\frac{VH}{dB}$
Also $I = ne AVa \Rightarrow Va = \frac{I}{ne A}$
 $\therefore \frac{I}{ne A} = -\frac{VH}{Bd} \Rightarrow VH = -\frac{1}{ne} \frac{IBd}{A}$
 $VH = \frac{-1}{ne} \frac{IBd}{Ax}$
Hall Coefficient $RH = -\frac{1}{ne}$
 $\therefore VH = RH \frac{IB}{x} \Rightarrow \therefore RH = \frac{VH}{IB}$

The simple formula for the Hall coefficient given above becomes more complex in semiconductors where the carriers are generally both electrons and holes which may be present in different concentrations and have different mobility.

For moderate magnetic field:
$$R_H = \frac{p u_h^2 - n u_e^2}{e(p u_h + n u_e)^2}$$

For large magnetic field: $R_H = \frac{1}{(p-n)e}$